

GI810 thru GI818

Vishay General Semiconductor

Glass Passivated Junction Fast Switching Rectifier

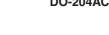
Major Ratings and Characteristics

I _{F(AV)}	1.0 A
V _{RRM}	50 V to 1000 V
I _{FSM}	30 A
t _{rr}	750 ns
I _R	10 µA
V _F	1.2 V
T _j max.	175 °C



technique is covered by Patent No. 3,996,602, and brazed-lead assembly by Patent No. 3,930,306

Mechanical Data



Case: DO-204AC, molded epoxy over glass body

Terminals: Matte tin plated leads, solderable per

E3 suffix for commercial grade, HE3 suffix for high

Epoxy meets UL-94V-0 Flammability rating

Polarity: Color band denotes cathode end

J-STD-002B and JESD22-B102D

reliability grade (AEC Q101 qualified)

Features

- · Superectifier structure for High Reliability condition
- · Cavity-free glass-passivated junction
- · Fast switching for high efficiency
- Low leakage current
- · High forward surge capability
- Solder Dip 260 °C, 40 seconds

Typical Applications

For general purpose of medium frequency rectification

Maximum Ratings

(T_A = 25 °C unless otherwise noted)

Parameter	Symbol	GI810	GI811	GI812	GI814	GI816	GI817	GI818	Unit
Maximum repetitive peak reverse voltage	V _{RRM}	50	100	200	400	600	800	1000	V
Maximum RMS voltage	V _{RMS}	35	70	140	280	420	560	700	V
Maximum DC blocking voltage	V _{DC}	50	100	200	400	600	800	1000	V
Maximum average forward rectified current 0.375" (9.5 mm) lead length at T_A = 75 °C	I _{F(AV)}	1.0							А
Peak forward surge current 8.3 ms single half sine-wave superimposed on rated load	I _{FSM}	30						A	
Operating junction and storage temperature range	T _J , T _{STG}	- 65 to + 175							°C

Pb

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Electrical Characteristics

(T_A = 25 °C unless otherwise noted)

Parameter	Test condition	Symbol	GI810	GI811	GI812	GI814	GI816	GI817	GI818	Unit
Maximum instantaneous forward voltage	at 1.0 A	V _F	1.2							V
Maximum DC reverse current at rated DC blocking voltage	T _A = 25 °C T _A = 100 °C	I _R	10 100							μA
Maximum reverse recovery time	I _F = 1.0 A, V _R = 30 V, di/dt = 50 A/μs	t _{rr}	750					ns		
Typical junction capacitance	at 4.0 V, 1 MHz	CJ	25						pF	

Thermal Characteristics

(T_A = 25 °C unless otherwise noted)

Parameter	Symbol	GI810	GI811	GI812	GI814	GI816	GI817	GI818	Unit
Typical thermal resistance ⁽¹⁾	R_{\thetaJA}	45							°C/W

Notes:

(1) Thermal resistance from junction to ambient at 0.375" (9.5 mm) lead length, P.C.B. mounted

Ratings and Characteristics Curves

(T_A = 25 °C unless otherwise noted)

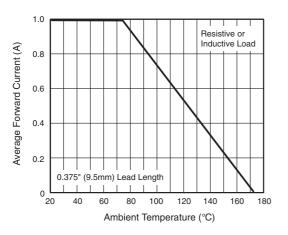


Figure 1. Forward Current Derating Curve

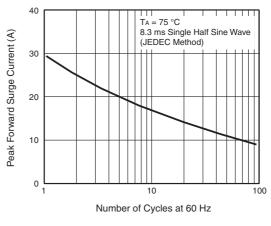


Figure 2. Maximum Non-repetitive Peak Forward Surge Current



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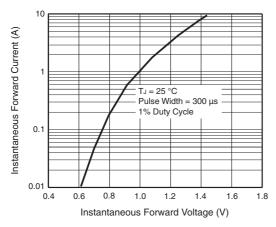


Figure 3. Typical Instantaneous Forward Characteristics

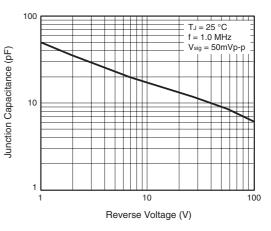
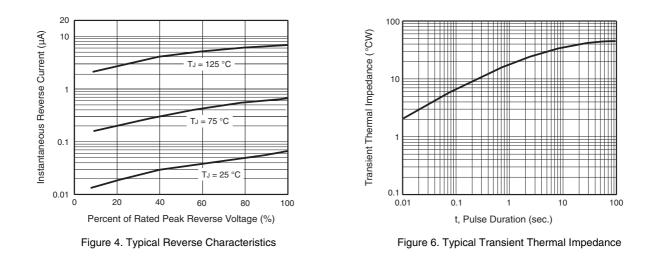
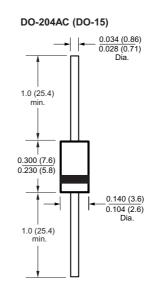


Figure 5. Typical Junction Capacitance



Package outline dimensions in inches (millimeters)





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